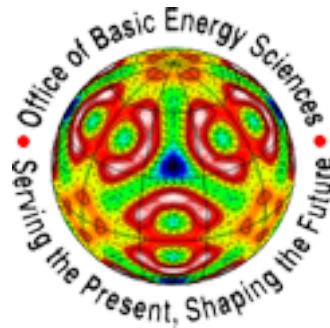


# Transport of Indirect Excitons in a Potential Energy Gradient

J.R. Leonard, M. Remeika, Y.Y. Kuznetsova, A.A. High, and L.V. Butov  
*Department of Physics, University of California at San Diego*

J. Wilkes  
*School of Physics and Astronomy, Cardiff University*

M. Hanson and A. C. Gossard  
*Materials Department, University of California at Santa Barbara*



# Indirect excitons

An exciton is a bound electron-hole pair.

*Indirect excitons:*  $e$  and  $h$  are confined to spatially separated quantum wells.

Properties of indirect excitons:

- increased lifetime and transport distance

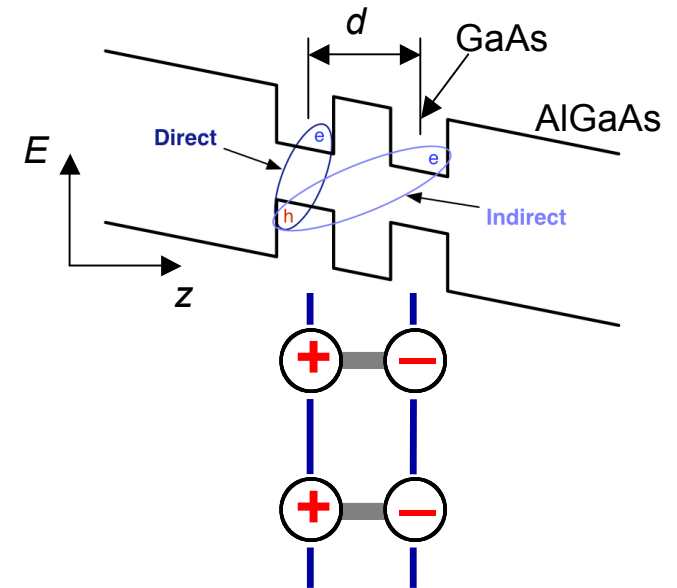
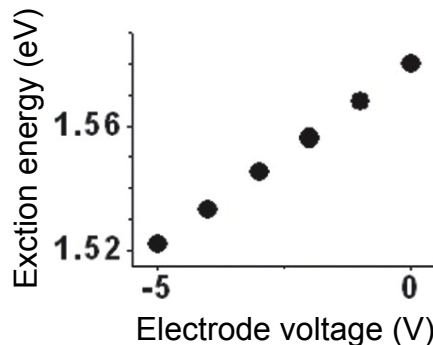
- oriented dipoles

repulsive interaction

excitons screen disorder

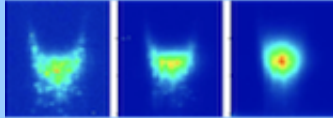
exciton energy controllable by applied voltage

$$\delta E = edF_z$$



# Excitonic devices

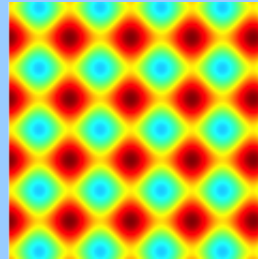
## Electrostatic traps for excitons



A.A. High *et al*, *Nano Lett.* **10**, 1021 (2012).

A.A. High, session FS 1  
4/8, 5:15 PM, rm. A4

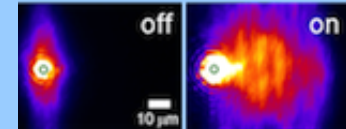
## Electrostatic lattices for excitons



M. Remeika *et al*, *APL* **100**, 061103 (2012).

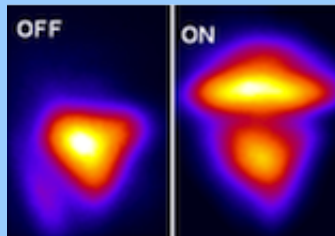
M. Remeika, session FS 4  
4/7, 12:15 PM, rm. A7

## Electrostatic conveyor for excitons



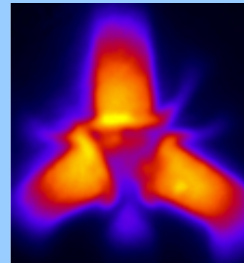
A.G. Winbow *et al*, *PRL* **106**, 196806 (2011).

## Exciton transistors



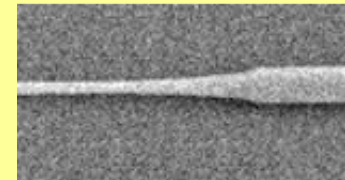
Y.Y. Kuznetsova *et al*, *Optics Lett.* **35**, 1587 (2010).

## Exciton integrated circuits



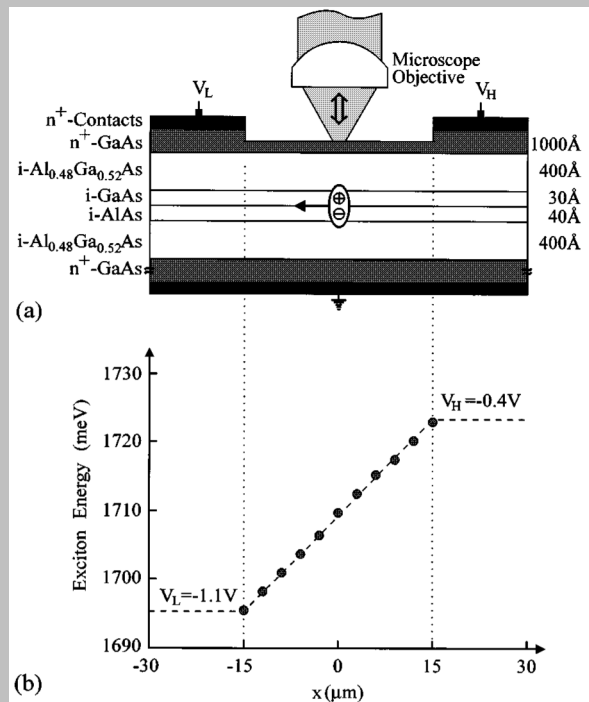
A.A. High *et al*, *Science* **321**, 229 (2008).

## New device: Exciton ramp (diode)



J.R. Leonard *et al*,  
arXiv:1203.6239v1 (2012)

## Earlier realizations of exciton ramps used voltage gradients



M. Hagn, A. Zrenner, G. Böhm,  
G. Weimann, *APL* **67**, 232 (1995)

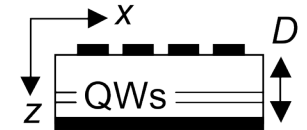
A. Gartner, A.W. Holleitner, J.P. Kotthaus,  
D. Schuh, *APL* **89**, 052108 (2006)

## New approach: Control of excitons by electrode density

Exciton energy landscape is controlled by using a single voltage on a single shaped electrode:

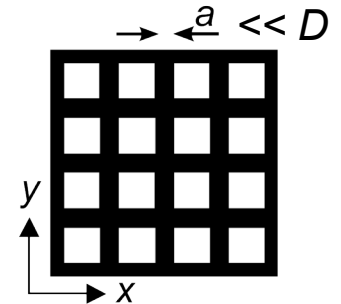
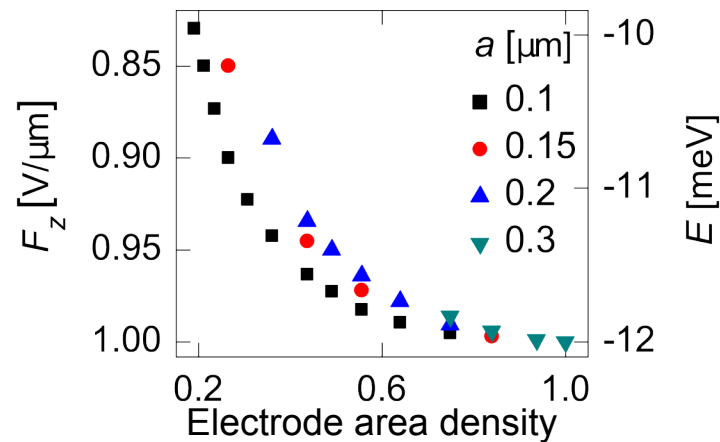
electrode pattern at voltage

ground plane



$$\delta E = edF_z$$

shaping the top electrode  
reduce  $F_z$  due to fringing field

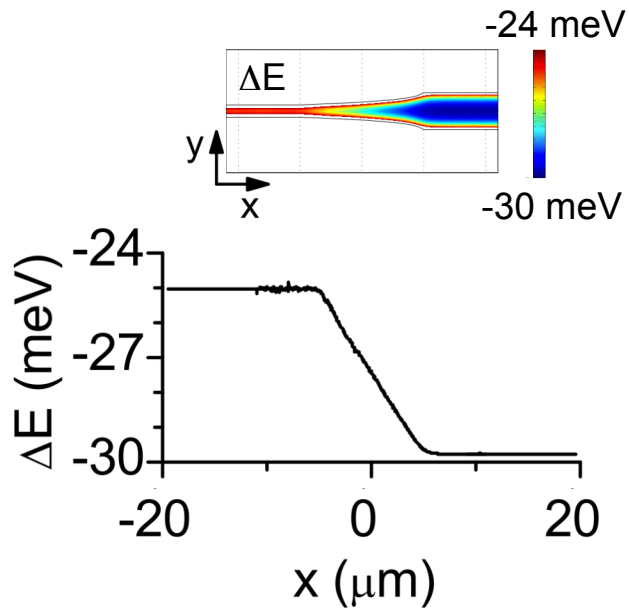


**Advantage:** suppression of heating by electric currents  
in electrodes

Y.Y. Kuznetsova, A.A. High, L.V. Butov, *APL* **97**, 201106 (2010)



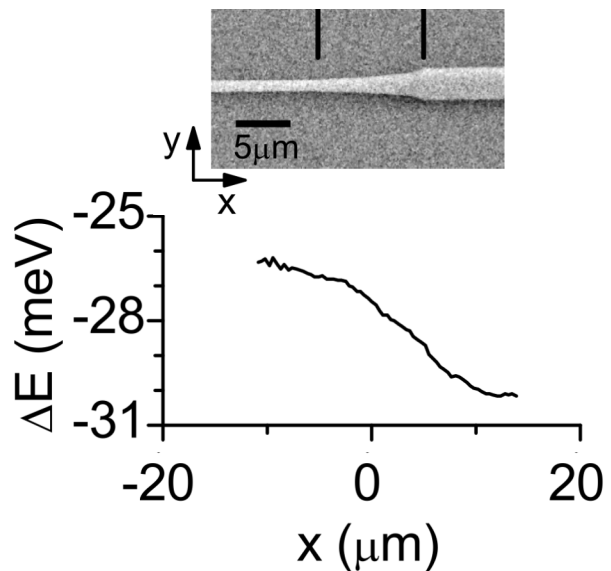
## Simulated energy profile



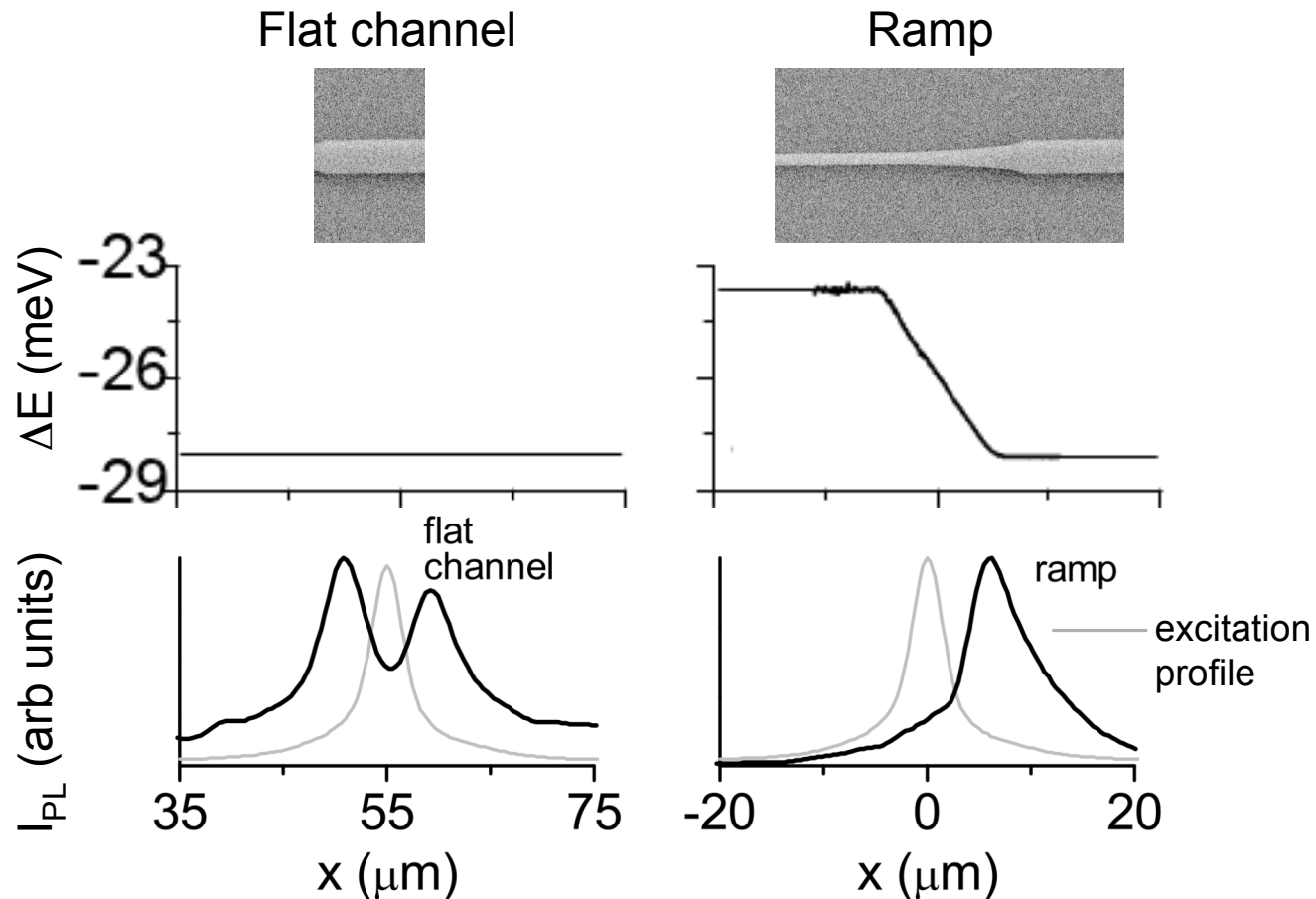
## Exciton ramps

- Width of electrode varies from 1  $\mu\text{m}$  to 3  $\mu\text{m}$
- Electrode shape calculated to give a linear potential energy profile for excitons

## Measured energy profile



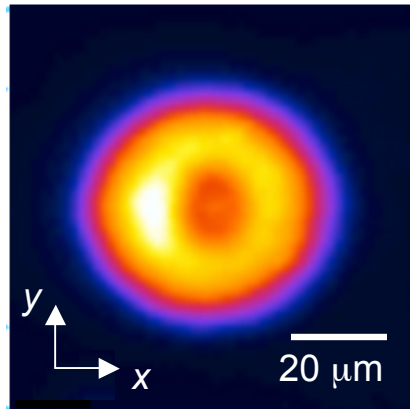
# Exciton transport in a ramp



**Flat channel:** exciton transport symmetric about the excitation spot

**Ramp:** exciton transport only in the direction of lower potential energy

➡ realizes directed transport of excitons as a diode realizes directed transport of electrons.



## Formation of the exciton inner ring

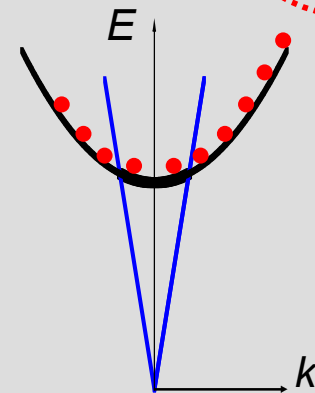
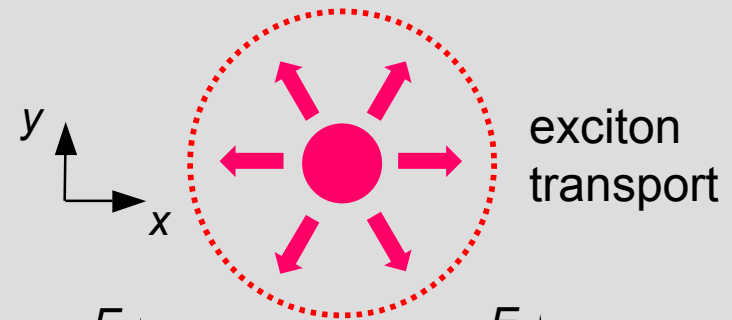
excitons cool as they travel away from the excitation spot

increased occupation of radiative zone

enhancement of PL intensity

inner ring

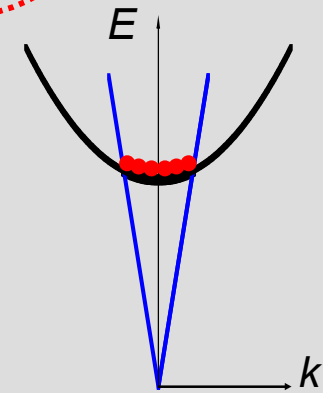
flow of excitons out of excitation spot due to exciton drift, diffusion, etc.



excitation spot

higher  $T_x$

lower occupation of radiative zone

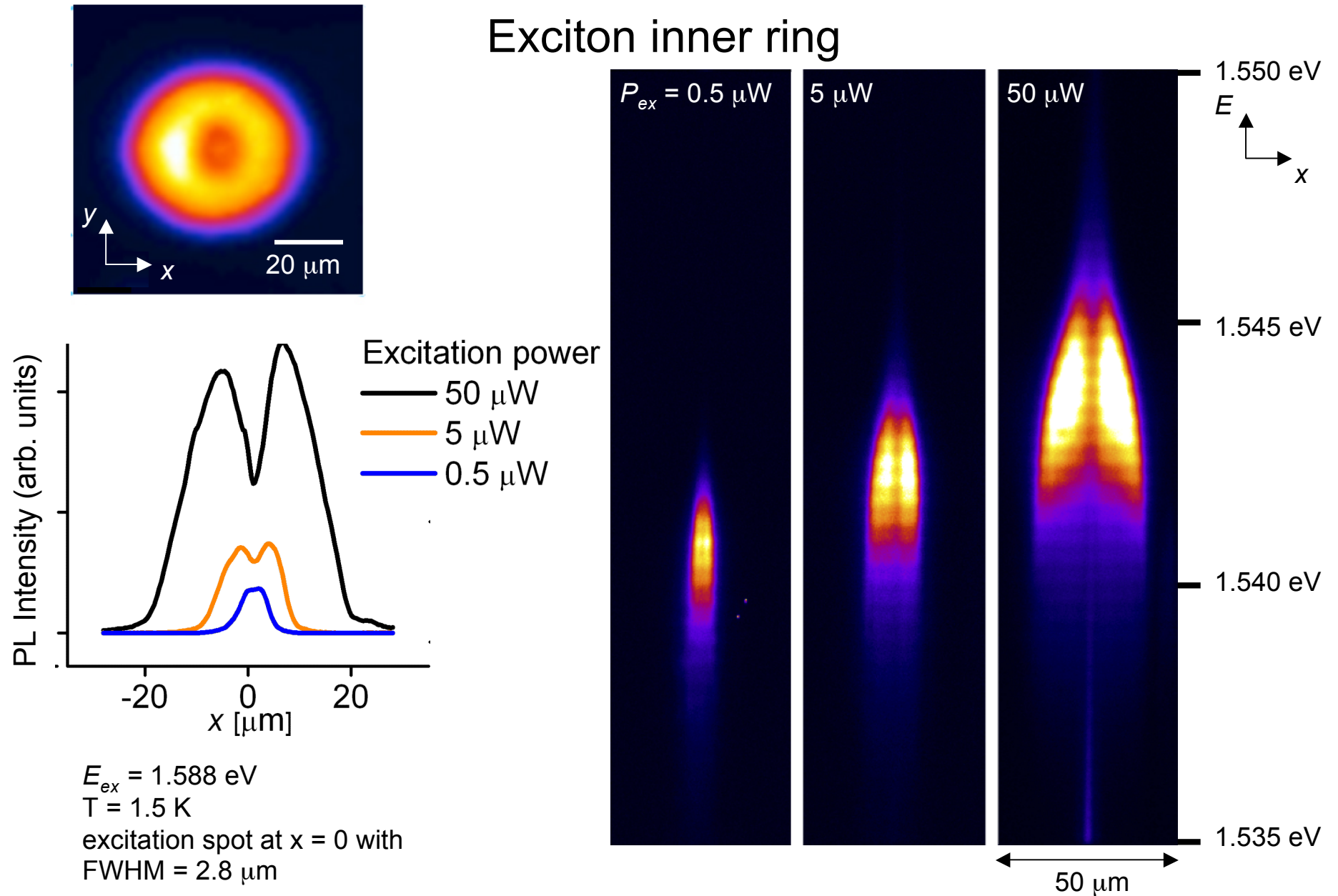


inner ring

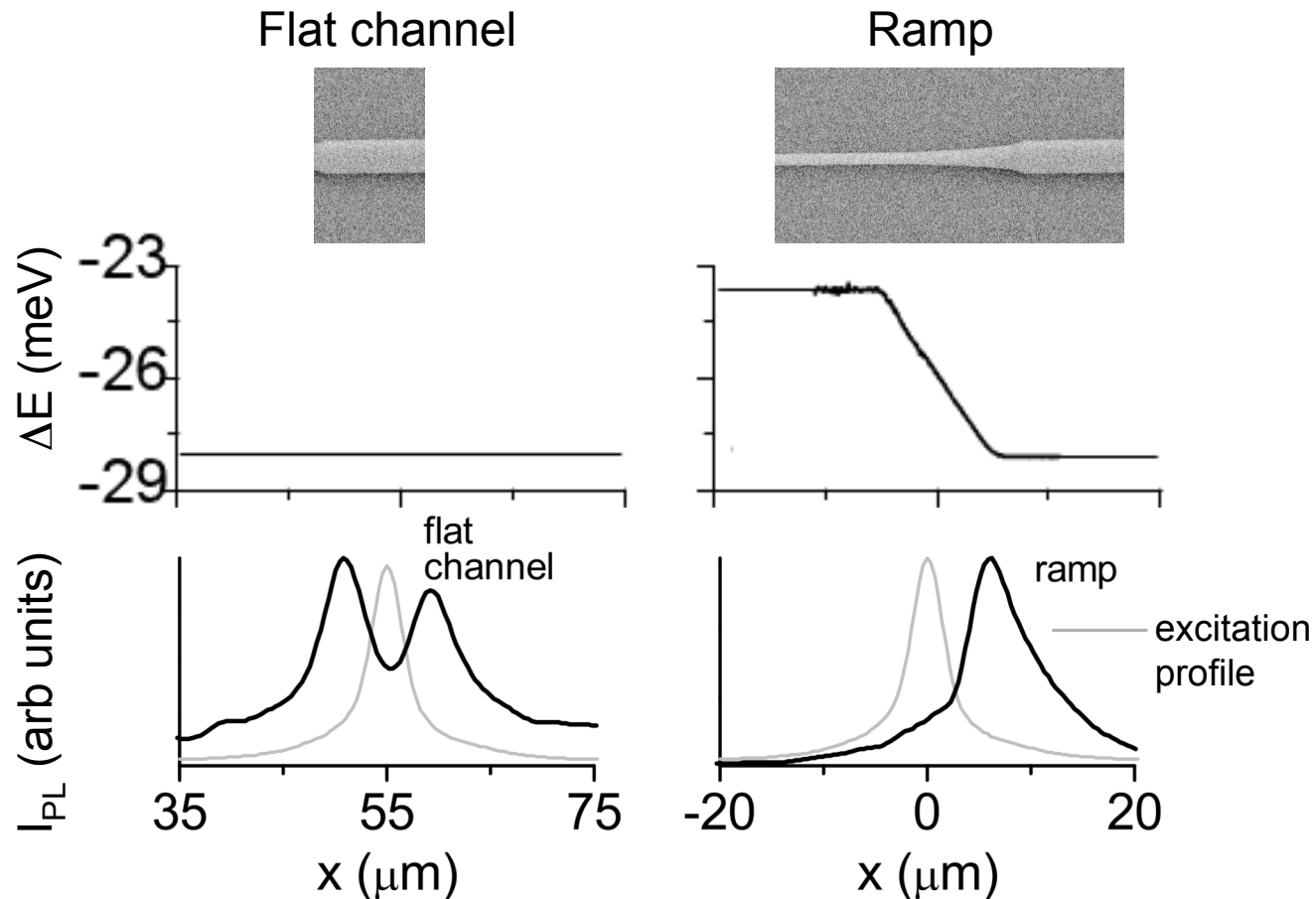
lower  $T_x$

higher occupation of radiative zone

## Exciton inner ring



# Exciton transport in a ramp

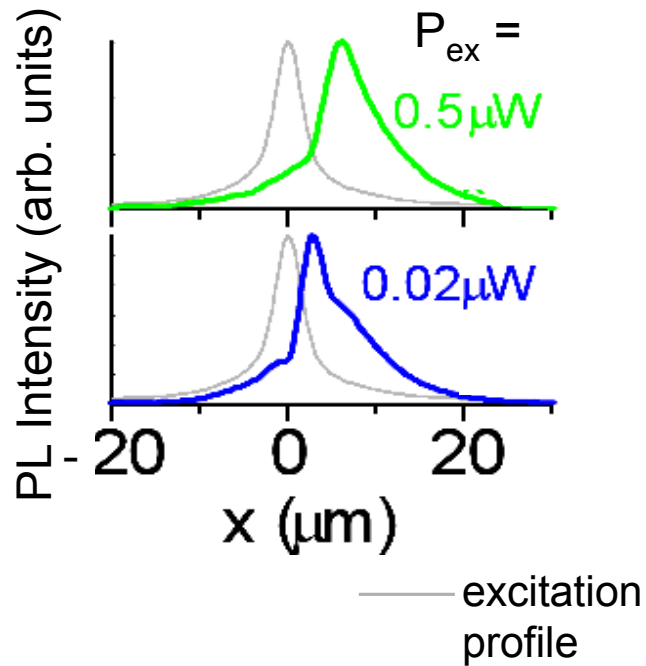


**Flat channel:** exciton transport symmetric about the excitation spot

**Ramp:** exciton transport only in the direction of lower potential energy

➡ realizes directed transport of excitons as a diode realizes directed transport of electrons.

# Density dependence of exciton transport in ramps



higher excitation power



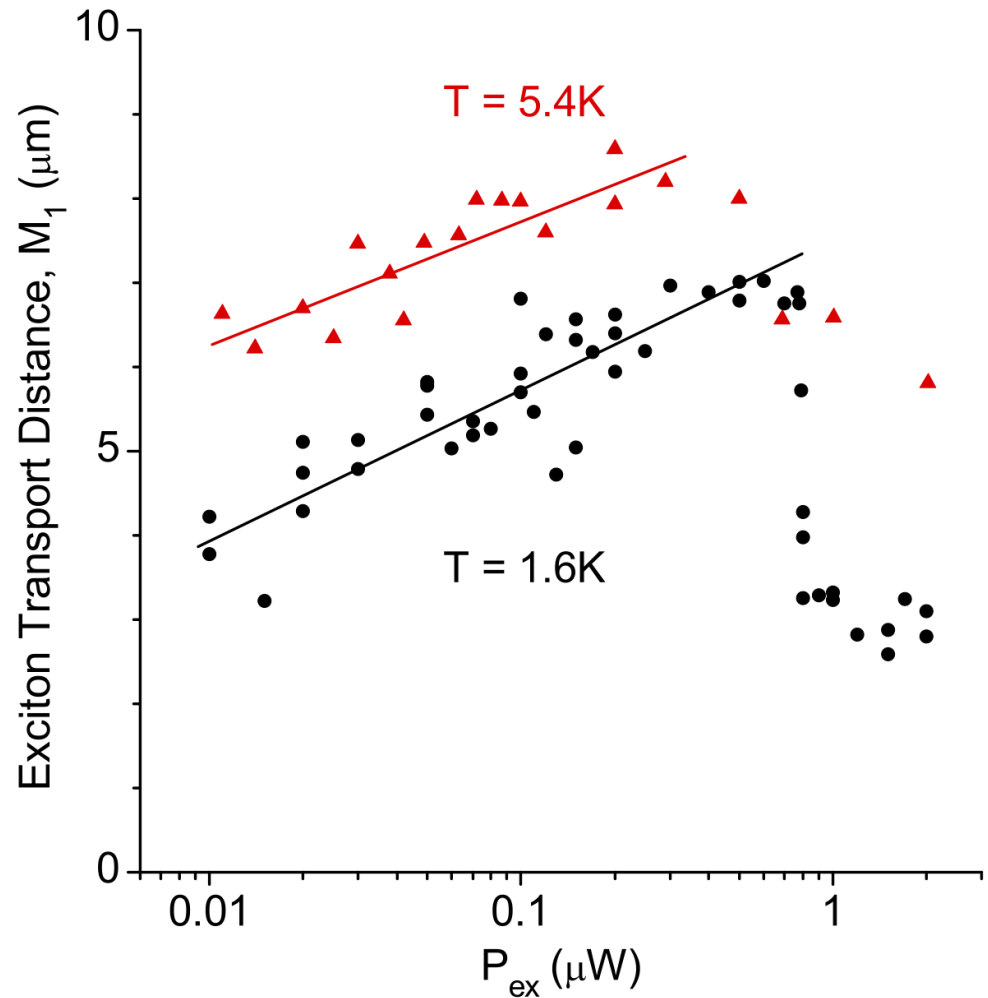
higher exciton density



better disorder screening



longer transport distances



# Numerical simulations

The system was modeled by solving coupled differential equations:

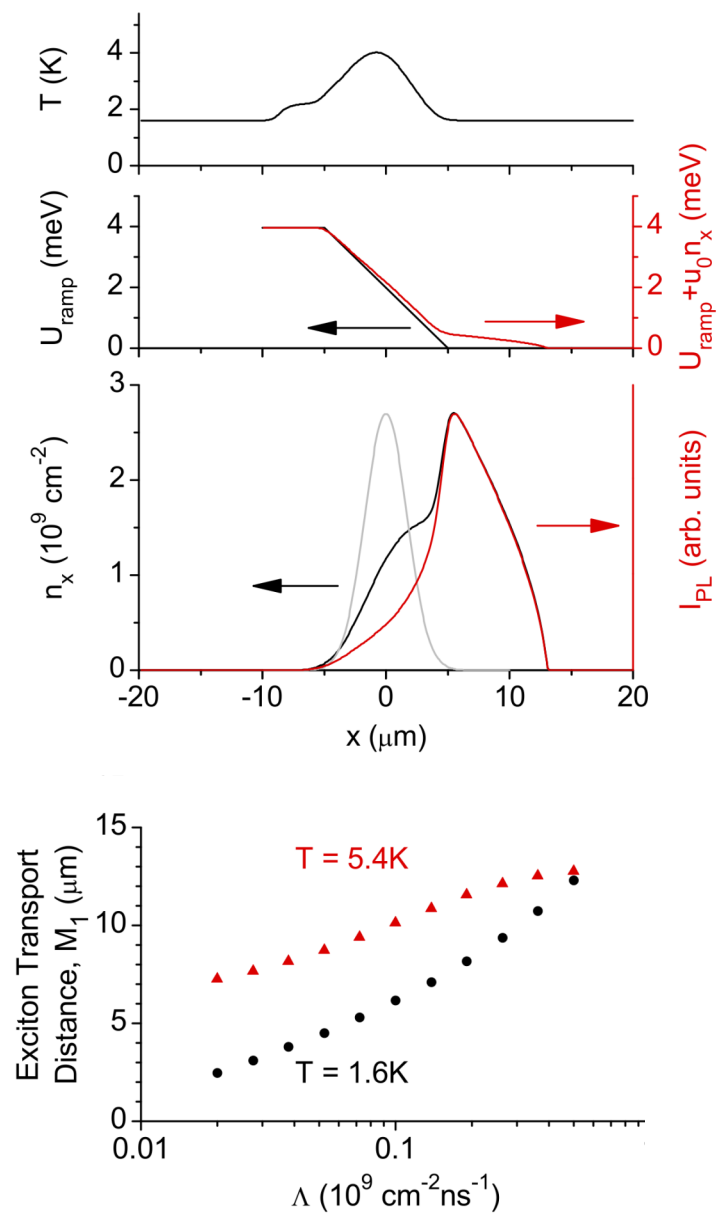
drift-diffusion equation

$$\nabla \left[ \underbrace{D_x \nabla n_x}_{\text{diffusion}} + \underbrace{\mu_x n_x \nabla (u_0 n_x + U_{ramp})}_{\text{drift}} \right] - \underbrace{n_x / \tau_{\text{opt}}}_{\text{optical decay}} + \underbrace{\Lambda}_{\text{exciton generation}} = 0$$

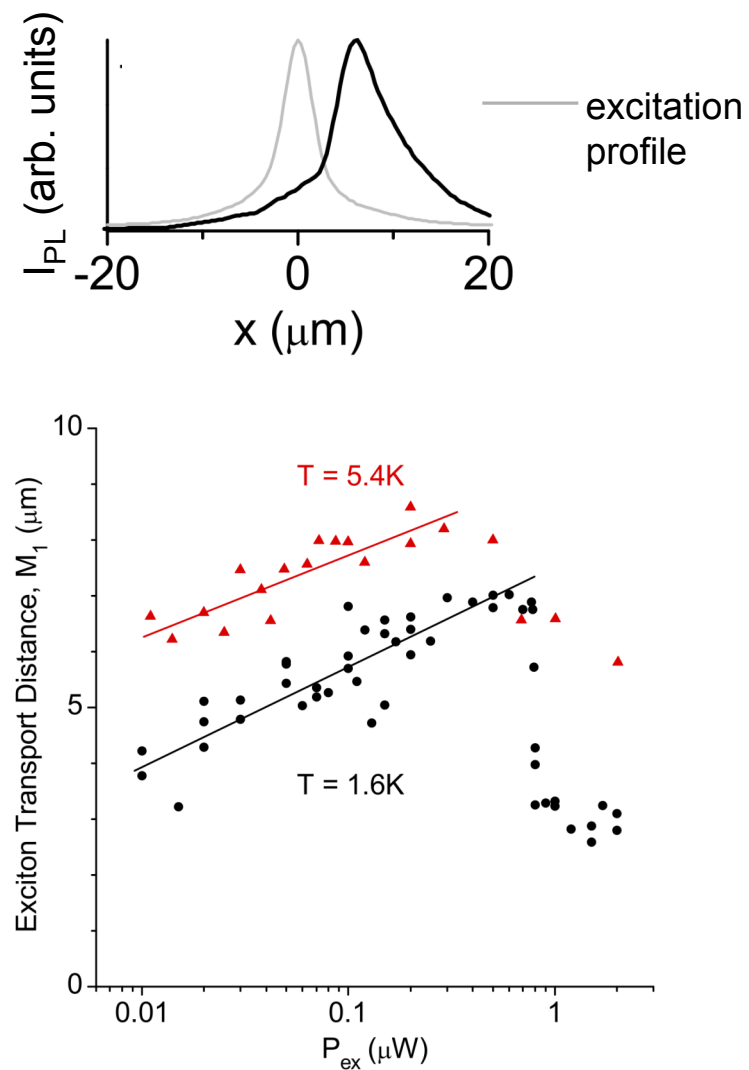
and heat balance equation

$$\underbrace{S_{\text{phonon}}(T_0, T)}_{\text{cooling through phonons}} = \underbrace{S_{\text{pump}}(T_0, T, \Lambda, E_{\text{inc}})}_{\text{heating due to laser}}$$

## Numerical simulations



## Experimental results





# Conclusions

- We realized a linear potential energy gradient (ramp) for indirect excitons using a shaped electrode at constant voltage.
- The excitonic ramp realizes directed transport of excitons as a diode realizes directed transport of electrons.
- We studied transport of indirect excitons along the ramp and observed that the exciton transport distance increases with increasing density and temperature.

J.R. Leonard, M. Remeika, Y.Y. Kuznetsova, A.A. High, L.V. Butov, J. Wilkes, M. Hanson and A.C. Gossard, arXiv:1203.6239v1 (2012).

